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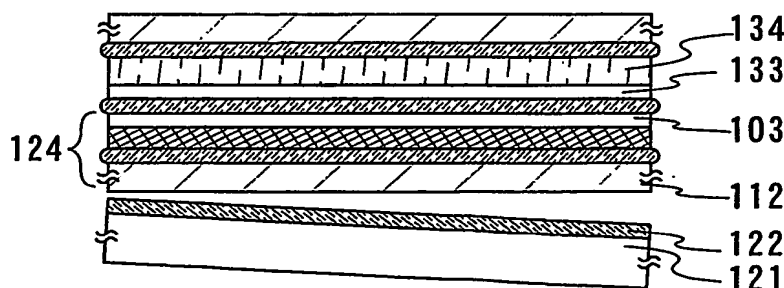
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(54) Title: METHOD OF MANUFACTURING DISPLAY DEVICE



(57) Abstract: To provide a method of  
manufacturing a display device having  
an excellent impact resistance property  
with high yield, in particular, a method  
of manufacturing a display device  
having an optical film that is formed  
using a plastic substrate. The method of  
manufacturing a display device includes  
the steps of: sequentially forming a  
metal film, an oxide film, and an optical  
filter on a first substrate; separating  
layers including the optical filter from  
the first substrate; attaching layers  
including the optical filter to a second

substrate; forming a layer including a pixel on a surface of a third substrate; attaching the layer including the pixel to a fourth  
substrate; and attaching layers including the optical filter to another surface of the third substrate.